

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1544	438/149.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 14:24
S1	2602	(TFT or (thin adj film adj transistor)) and electrode and insulat\$3 and (gate with (sidewall or (side adj wall) or (side adj surface)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 14:24
S2	2235	S1 and (insulat\$3 with substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:14
S3	1976	S2 and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:14
S4	838	S3 and (TFT or (thin adj film adj transistor)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:14
S5	230	S4 and side.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:15
S6	111	S5 and thin.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:16
S7	110	S6 and (gate with side)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:17
S8	93	S6 and (gate with side).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:26
S9	11	S8 and (slant\$3 or slop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:18

S10	2	S8 and asymmetric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:26
S11	9	("3493812" "4547789").PN. OR ("4924279").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/08 17:37
S12	12	("4547789").URPN.	USPAT	OR	ON	2005/12/08 17:45